

elements of  
**INFRARED  
TECHNOLOGY**  
generation, transmission, and detection

KRUSE • McGLAUCHLIN • McQUISTAN

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**PAUL W. KRUSE**  
Staff Scientist

**LAURENCE D. McGLAUCHLIN**  
Research Section Head

**RICHMOND B. McQUISTAN**  
Staff Scientist  
Honeywell Research Center

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